

AMENDMENTS TO THE SPECIFICATION

In accordance with 37 C.F.R. § 1.121(b)(1), delete the paragraph appearing at page 7, lines 12-21 of the specification, and replace that paragraph with a replacement paragraph as follows:

A semiconductor device 28 is directly electrically interconnected to the chip attach sites 24 as shown in FIGS. 6A and 6B. By "directly" it is meant that the interconnection is by a flip chip method without the use of an intervening wire bond or tape automated bonding (TAB) tape. Suitable attachments 30 include solders with a primary constituent selected from the group consisting of gold, tin and lead with a melting temperature in the range of between 180 °C. and 240 °C. The spacing 32 between the semiconductor device 28 and routing circuits 26 is preferably at least 75 microns, and preferably between 100 and 150 microns to facilitate the flow of a second molding compound, as detailed below. Preferably, 50% to 75% (in height) of the spacing 32 is due to the chip attach pillar 34 and 50%-25% (in height) of the spacing is due to attachment 30.